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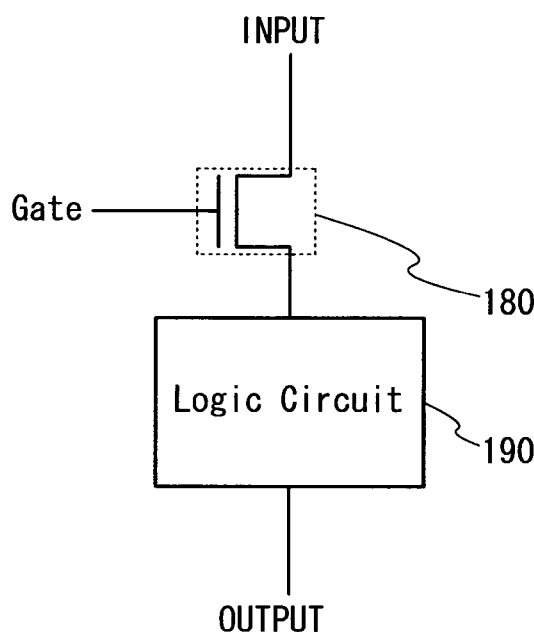
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(54) Title: SEMICONDUCTOR DEVICE

FIG. 1A



(57) Abstract: The semiconductor device includes: a transistor having an oxide semiconductor layer; and a logic circuit formed using a semiconductor material other than an oxide semiconductor. One of a source electrode and a drain electrode of the transistor is electrically connected to at least one input of the logic circuit, and at least one input signal is applied to the logic circuit through the transistor. The off-current of the transistor is preferably 1×10^{-13} A or less.

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